Silicon NPN Epitaxial

# HITACHI

ADE-208-392 1st. Edition

#### Application

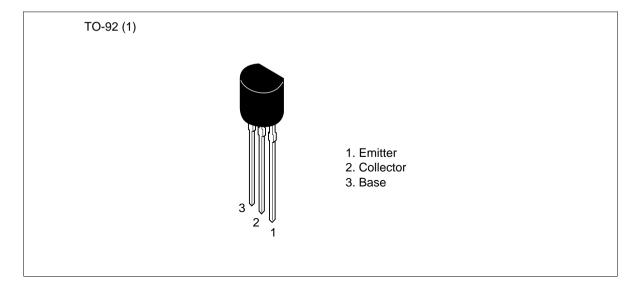
- Wide band video output amplifier for color CRT monitor.
- High frequency high voltage amplifier.
- High speed power switching.
- Complementary pair with 2SC5225.

#### Features

- High voltage large current operation.  $V_{CEO} = -80 \text{ V}, I_C = -300 \text{ mA}$
- High f<sub>T</sub>.
  - $f_{\rm T} = 1.3 \; GHz$
- Small output capacitance. Cob = 2.9 pF



## Outline



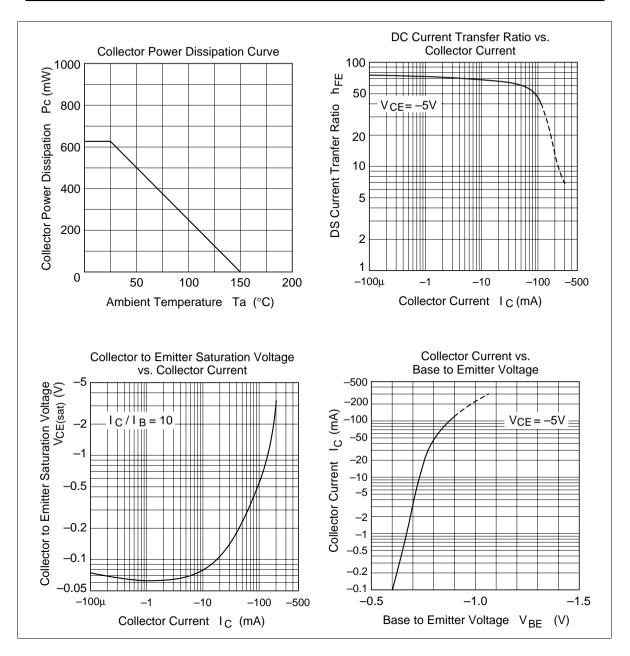
# **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-80	V
Collector to emitter voltage	V <sub>CEO</sub>	-80	V
Emitter to base voltage	V <sub>EBO</sub>	-3	V
Collector current	I <sub>c</sub>	-300	mA
Collector power dissipation	P <sub>c</sub>	625	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

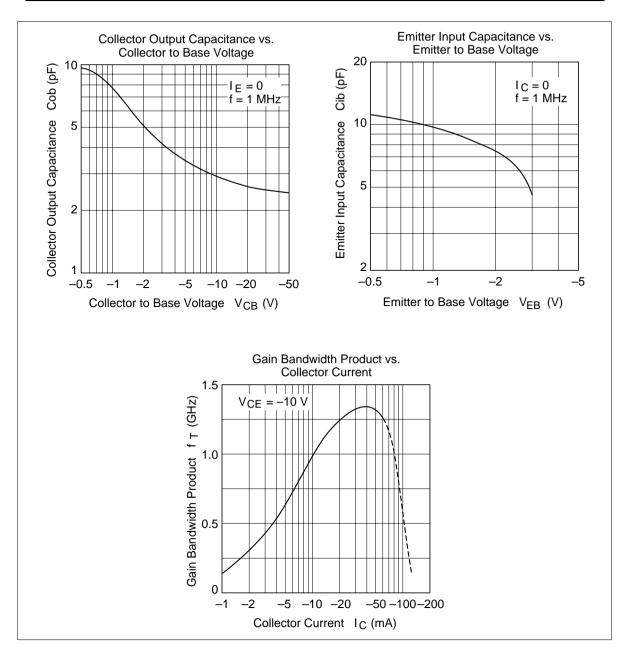
# **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	-80	_	_	V	$I_{c} = -100 \ \mu A$ $I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	-80	_	_	V	$I_{c} = -1 \text{ mA}$ $R_{BE} = \infty$
Collector to base cutoff current	I <sub>CBO</sub>	_	_	-1.0	μΑ	$V_{CB} = -60 \text{ V}$ $I_E = 0$
Emitter to base cutoff current	I <sub>EBO</sub>	_	_	-10	μΑ	$V_{EB} = -3 V$ $I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub>	20	60	—		$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -50 \text{ mA}$ Pulse test
Gain bandwidth product	f <sub>T</sub>	1.1	1.3	—	GHz	$V_{ce} = -10 \text{ V}$ $I_c = -50 \text{ mA}$
Emitter input capacitance	Cib	—	14.5	18	pF	$V_{EB} = 0$ , $I_{C} = 0$ f = 1 MHz
Collector output capacitance	Cob	—	2.9	4.0	pF	$V_{CB} = -10 \text{ V}, I_E = 0$ f = 1 MHz

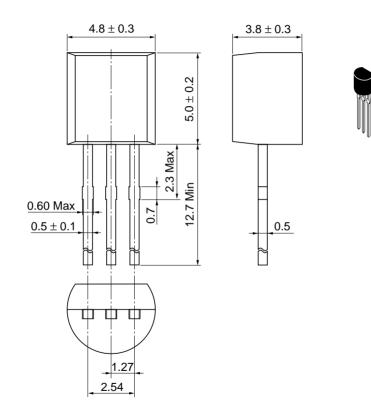
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Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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